

**AMENDMENTS TO THE CLAIMS**

**Please cancel claims 9-10 without prejudice or disclaimer and amend the claims as follows:**

1. (Previously Presented) A Group III nitride semiconductor light-emitting element including an n-type contact layer of n-type GaN, an n-type clad layer of n-type  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 < x < 1$ ), an active layer, a p-type clad layer, and a p-type contact layer, comprising:

a crack-preventing layer of n-type GaN provided between the n-type contact layer and the n-type clad layer,

wherein the crack-preventing layer has a dopant concentration lower than that of the n-type contact layer, the dopant concentration of the crack-preventing layer being within a range of  $5 \times 10^{16} \text{ cm}^{-3}$  to  $5 \times 10^{17} \text{ cm}^{-3}$ .

2.-3. (Canceled)

4. (Original) The light-emitting element according to claim 1, wherein the n-type contact layer has a dopant concentration within a range of  $4 \times 10^{18} \text{ cm}^{-3}$  to  $2 \times 10^{19} \text{ cm}^{-3}$ .

5. (Original) The light-emitting element according to claim 1, wherein a dopant of the crack-preventing layer is either one of Si and Ge.

6. (Original) The light-emitting element according to claim 1, wherein a dopant of the n-type contact layer is either one of Si and Ge.

7.-10. (Canceled)